



## DOCUMENT CHANGE REQUEST

DCR number 1091 Changes required for: General

Date: 2017/09/26

Date sent: 2017/06/05

Originator: Samuel Savin

Organisation: STMicroelectronics

Status: IMPLEMENTED

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH8N10

Number: 5205/023

Issue:

4

Other documents affected:

Page:

11

Paragraph:

2.4.1 Room Temperature Electrical Measurements

Original wording:

See document an attachment.

Proposed wording:

See document an attachment.

Justification:

See document an attachment.



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Other documents affected:

Page:

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Paragraph:

2.10.2

Original wording:

see published specification

Proposed wording:

The same change to Qgd limit (i.e. to be 4.3nC min / 6.5nC max) introduced in th is DCR shall also apply to the table in Para 2.10.2 (irradiation electrical measurements).

Justification:

Attachments:

dcr\_strh8n10.pdf

Modifications:

The same change to Qgd limit (i.e. to be 4.3nC min / 6.5nC max) shall also apply to the table in Para 2.10.2 (irradiation electrical measurements).

Approval signature:

Date signed:

2017-09-26